

/ Descriptions

Silicon PNP transistor in a SOT-323 Plastic Package.

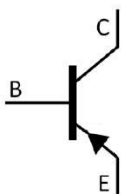
/ Features

High current, low voltage complementary pair with BC848W.

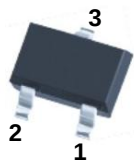
/ Applications

General purpose switching and amplification.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter

PIN 2 Base

PIN 3 Collector

/ Marking

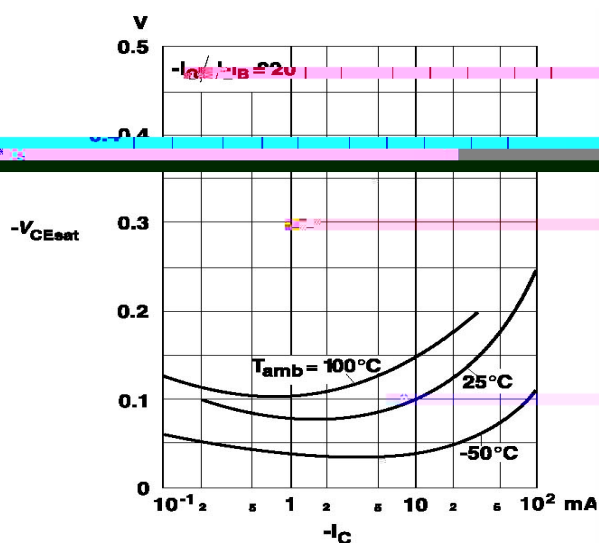
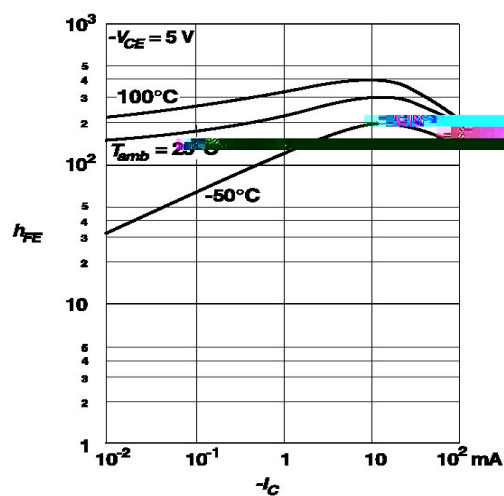
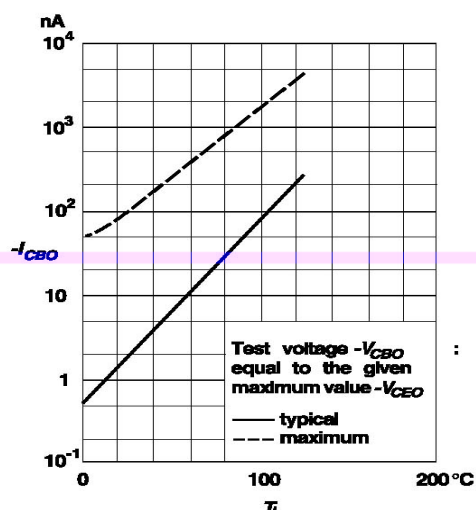
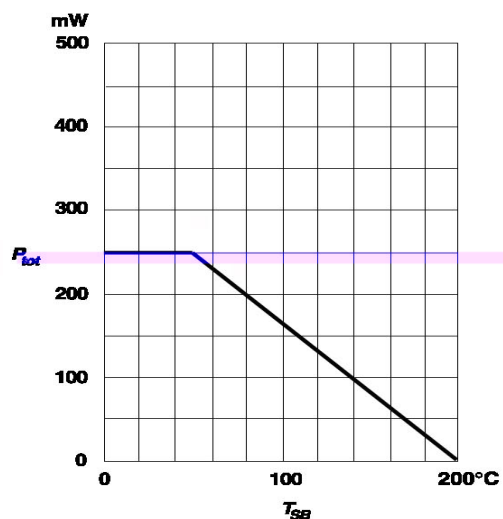
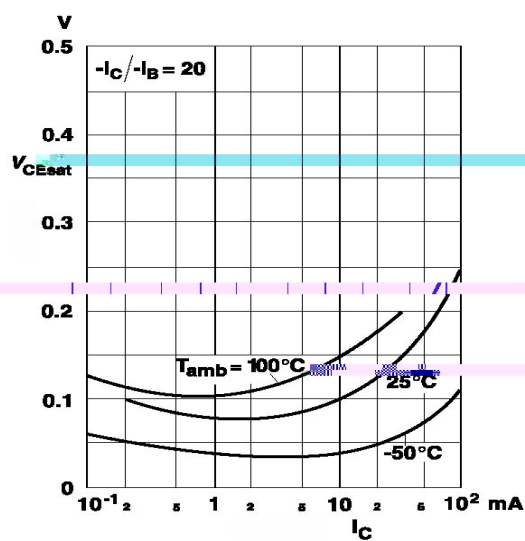
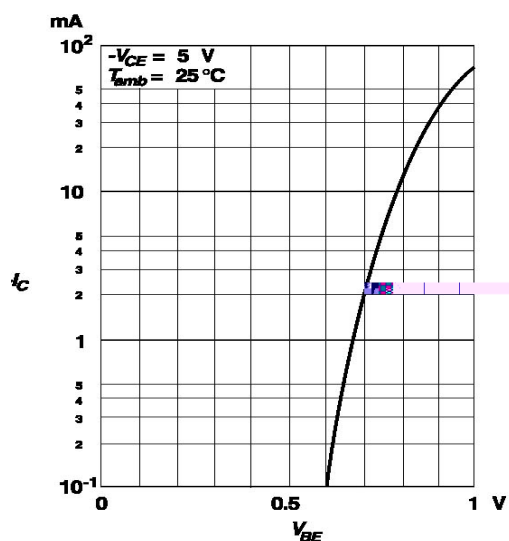
h_{FE} Classifications Symbol	A	B	C
h_{FE} Range	125 250	220 475	420 800
Marking	H3J	H3K	H3L

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Peak Collector Current - Continuous	I_{CM}	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

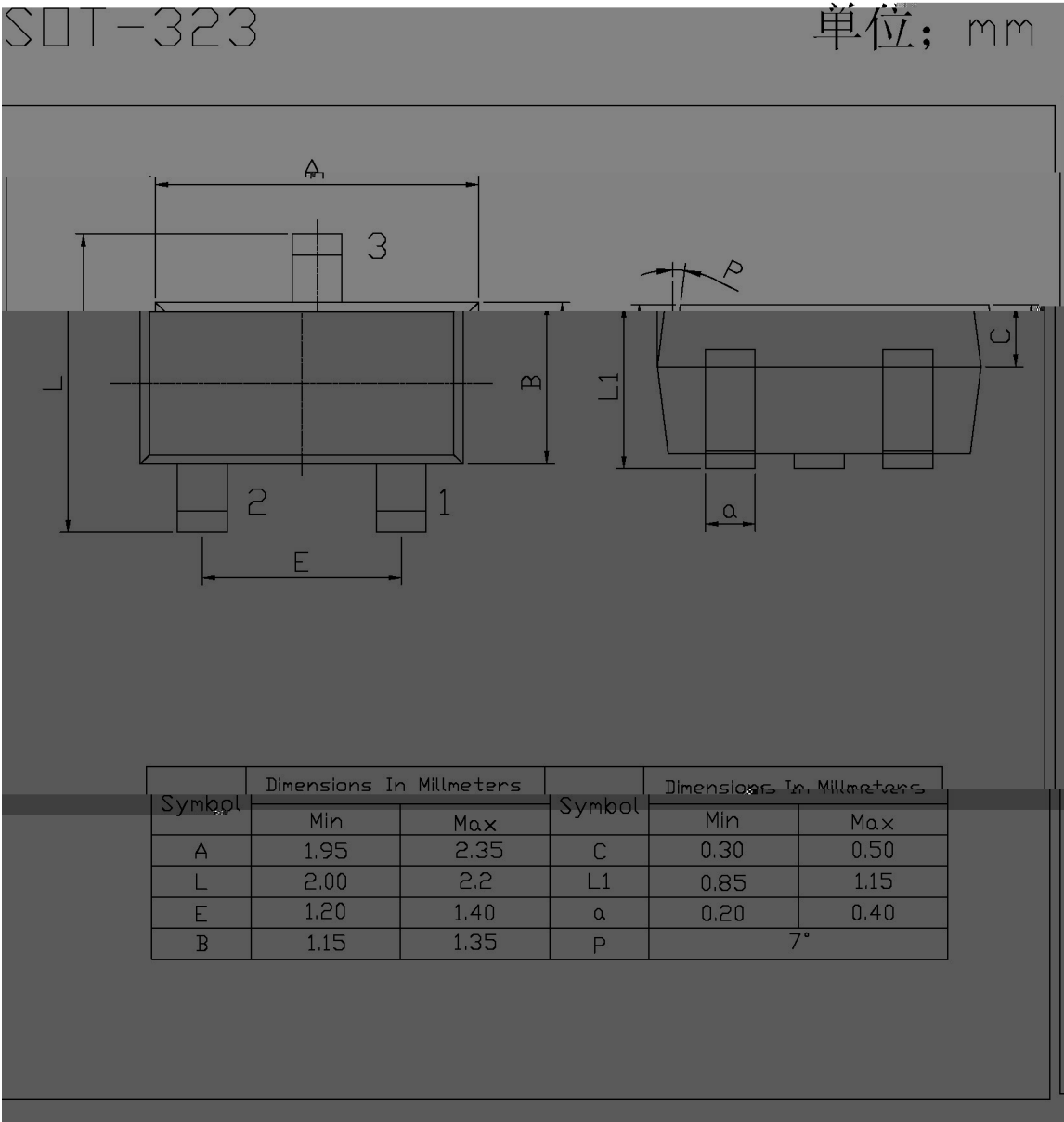
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.015	A
Emitter to Base Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	A
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-2.0mA$	125		800	

Collector to Emitter Saturation Voltage $V_{CE(sat)(1)}$ I

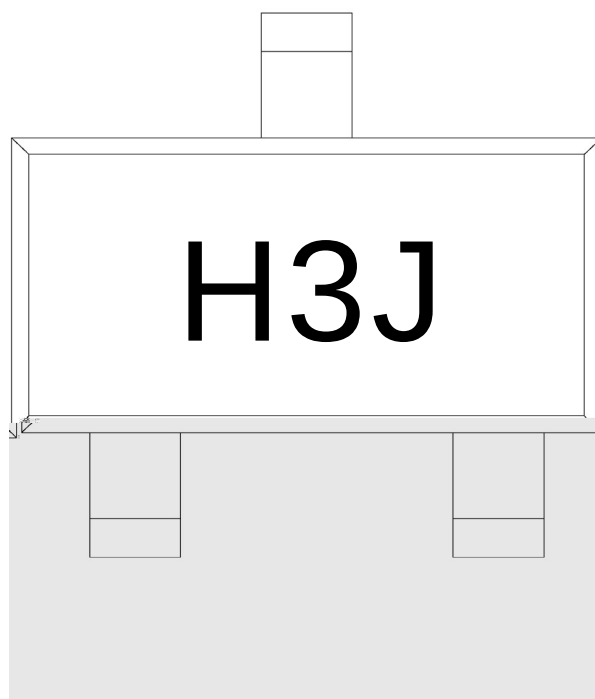
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



H

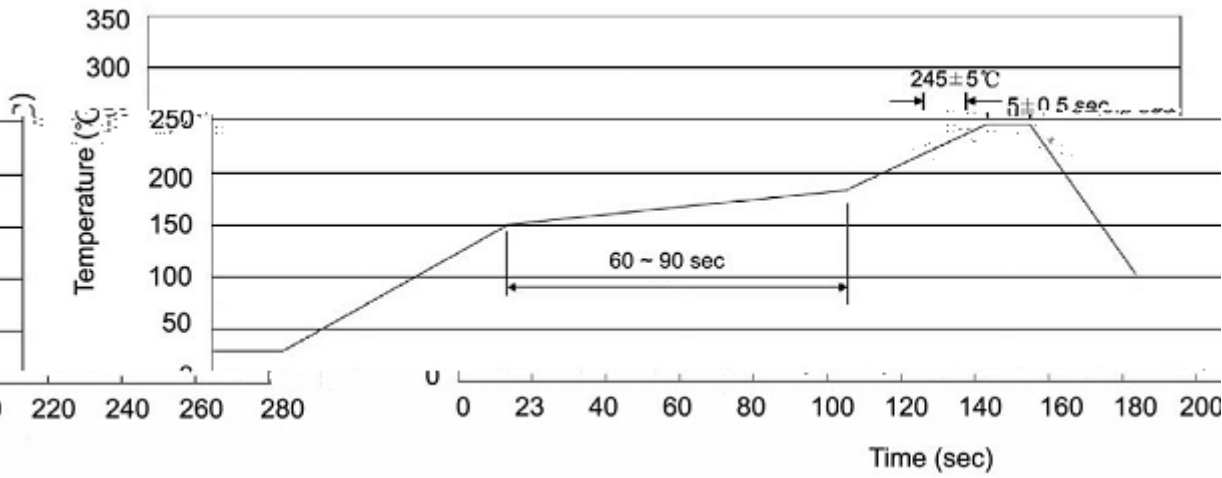
3J

Note:

H: Company Code.

3J: Product Type.

() / Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0lueh,



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices